

GRF2076

Ultra-Low Noise Amplifier with Bypass 600 to 7125 MHz

FEATURES

- Flexible Bias Voltage and Current
- Process: GaAs pHEMT
- Single Control Logic Input
- Internally Matched to 50 Ω
- Compact 1.5 x 1.5 mm DFN-6 Package

Reference: 5 V / 70 mA / 3.6 GHz

- Gain: 17.2 dB
- OP1dB: 22 dBm
- OIP3: 38 dBm
- Evaluation Board Noise Figure: 1.1 dB
- Bypass Mode Gain: -2 dB
- Bypass Mode OP1dB: 21 dBm
- Bypass Mode OIP3: 46 dBm

APPLICATIONS

- Cellular Repeaters and Signal Boosters
- Cellular Infrastructure
- CBRS

DESCRIPTION

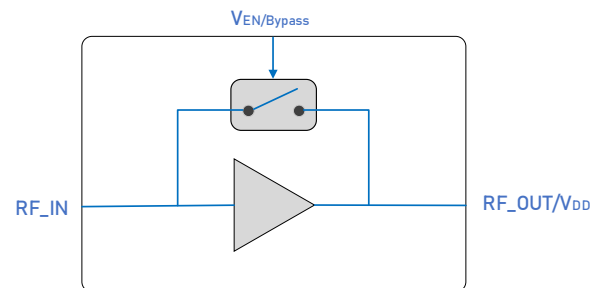
The GRF2076 is an ultra-low noise amplifier with bypass for small cell, wireless infrastructure, and other high-performance applications. It exhibits high gain, outstanding noise figure (NF), and linearity from 600 to 6000 MHz using band-specific matching, and fractional bandwidths of up to 45%.

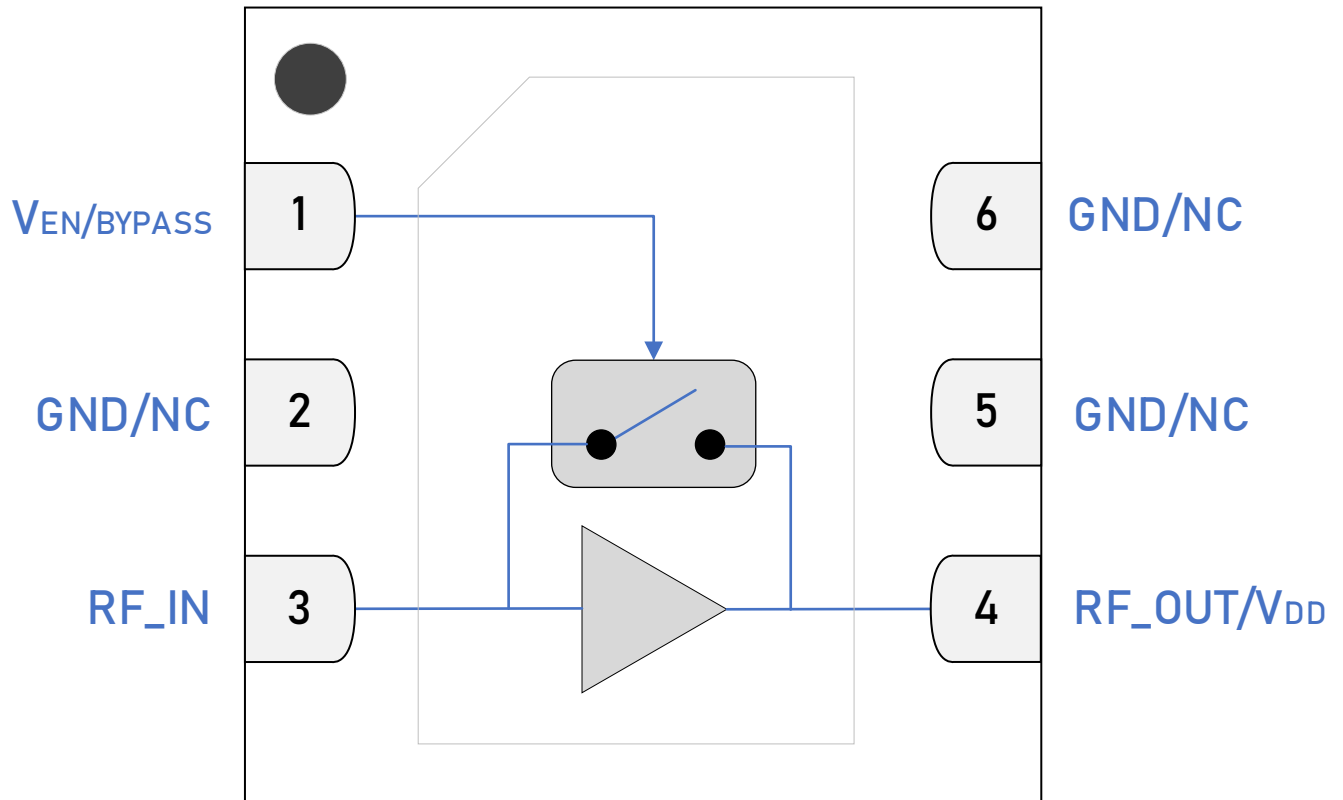
The device can be operated from a supply voltage of 2.7 to 6 V with a selectable I_{DDQ} range of 20 to 100 mA for optimal efficiency and linearity.

Please consult with the GRF applications engineering team for custom tuning/evaluation board data and device S-parameters.

Additional tunes can be found on the GRF2076 "Custom Tunes" product page: [GRF2076 Custom Tunes](#)

BLOCK DIAGRAM





1.5 x 1.5 mm DFN-6 Pin Out (Top View)

Pin Assignments

Pin	Name	Description	Note
1	V _{ENABLE/BYPASS}	V _{EN/BYPASS} Voltage Input	V _{EN/BYPASS} ≤ 0.2 volts sets Bypass Mode. V _{EN/BYPASS} and external series resistor control the device I _{DDQ} when V _{EN/BYPASS} is high.
2, 5, 6	GND/NC	Ground or No Connect	No internal connection to die. We recommend connecting these pins to ground.
3	RF_IN	RF Input	Internally matched to 50 Ω. An external DC blocking capacitor must be used.
4	RF_OUT/ V _{DD}	RF Output	Internally matched to 50 Ω. V _{DD} must be applied through a choke to this pin.
PKG BASE	GND	Ground	Provides DC and RF ground for device, as well as thermal heat sink. Recommend multiple 8 mil vias beneath the package for optimal RF and thermal performance. Refer to evaluation board top layer graphic on schematic page.

Control Logic Truth Table

Mode	Description	V _{DD}	V _{EN/BYPASS}
High Gain	High Gain	1	1
Bypass	Linear Bypass Mode	1	0
Logic Level "0"	Logic Low	0 V to 0.2 V	0 V to 0.2 V
Logic Level "1"	Logic High	1.8 V to 5 V	1.5 V to V _{DD}

Absolute Ratings

Parameter	Symbol	Min.	Max.	Unit
Supply Voltage	V_{DD}	0	6	V
RF Input Power: Load VSWR < 2:1, $V_{DD} = 5$ V, $V_{EN/BYPASS} = 5$ V (Gain Mode)	$P_{IN\ MAX}$		27	dBm
RF Input Power: Load VSWR < 2:1, $V_{DD} = 5$ V, $V_{EN/BYPASS} = 0$ V (Bypass Mode)	$P_{IN\ MAX}$		27	dBm
Operating Temperature (Package Base)	$T_{PKG\ BASE}$	-40	115	°C
Maximum Channel Temperature (MTTF > 10 ⁶ hours)	T_{MAX}		170	°C
Maximum Dissipated Power	$P_{DISS\ MAX}$		330	mW

Electrostatic Discharge

Human Body Model	HBM	1000		V
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Storage

Storage Temperature	T_{STG}	-65	150	°C
Moisture Sensitivity Level	MSL		1	--



Caution! ESD Sensitive Device.

Exceeding Absolute Maximum Rating conditions may cause permanent damage.

Note: For additional information, please refer to *Package Manufacturing Information* | *Guerrilla RF* (guerrilla-rf.com)



All Guerrilla RF products are provided in RoHS compliant lead (Pb)-free packaging requiring no exemptions. Additional information for this topic can be found at this link - *Environmental and Restricted Substance Statement Library*

Recommended Operating Conditions

Parameter	Symbol	Specification			Unit	Condition
		Min.	Typ.	Max.		
Supply Voltage	V _{DD}	2.7	5	6	V	
Operating Temperature (Package Base)	T _{PKG BASE}	-40		115	°C	
RF Frequency Range	F _{RF}	600	3.6	7125	MHz	Typical Application Schematic with external matching components (notes 1 & 2).
RF_IN Port Impedance	Z _{RFIN}		50		Ω	Single-ended with 2-element match.
RF_OUT Port Impedance	Z _{RFOUT}		50		Ω	Single-ended with 2-element match.

Note 1: Operation outside of this range is supported by using different custom tunes. Examples of other optimized tunes can be found here: [GRF2076 Custom Tunes](#)

Note 2: Contact the Guerrilla RF Applications team for guidance on optimizing the tuning of the device for alternative bands.

Nominal Operating Parameters – General

The following conditions apply unless noted otherwise: Typical Application Schematic using the 3.3 to 3.8 GHz tuning set. $V_{DD} = 5\text{ V}$, $V_{EN/BYPASS} = 5\text{ V}$, $I_{DDQ} = 70\text{ mA}$. $F_{TEST} = 3.6\text{ GHz}$. $M5 = 600\ \Omega$. $T_{PKG\ BASE} = 25\text{ }^\circ\text{C}$. Evaluation board losses are included within the specifications.

Parameter	Symbol	Specification			Unit	Condition
		Min.	Typ.	Max.		
Supply Current	I_{DDQ}		70		mA	$V_{DD} = 5\text{ V}$, $V_{EN/BYPASS} = 5\text{ V}$
Enable Current	I_{ENABLE}		3	10	mA	$V_{DD} = 5\text{ V}$, $V_{EN/BYPASS} = 5\text{ V}$
Switching Rise Time	T_{RISE}		200		ns	Bypass Mode to Gain Mode. Pin = +5.8 dBm (note 3).
Switching Fall Time	T_{FALL}		50		ns	Gain Mode to Bypass Mode. Pin = +5.8 dBm (note 4).

Disabled Mode

Leakage Current	$I_{LEAKAGE}$		600	1000	μA	$V_{DD} = 5\text{ V}$, $V_{EN/BYPASS} = 0\text{ V}$
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Thermal Data

Thermal Resistance: (Infrared Scan)	Θ_{JC}		66		$^\circ\text{C}/\text{W}$	On Standard Evaluation Board (note 5).
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Note 3: Switching Time: 50% of $V_{EN/BYPASS}$ to 90% of P_{out} .

Note 4: Switching Time: 50% of $V_{EN/BYPASS}$ to 10% of P_{out} .

Note 5: $MTTF > 10^6$ hours for $T_{CHANNEL} \leq 170\text{ }^\circ\text{C}$.

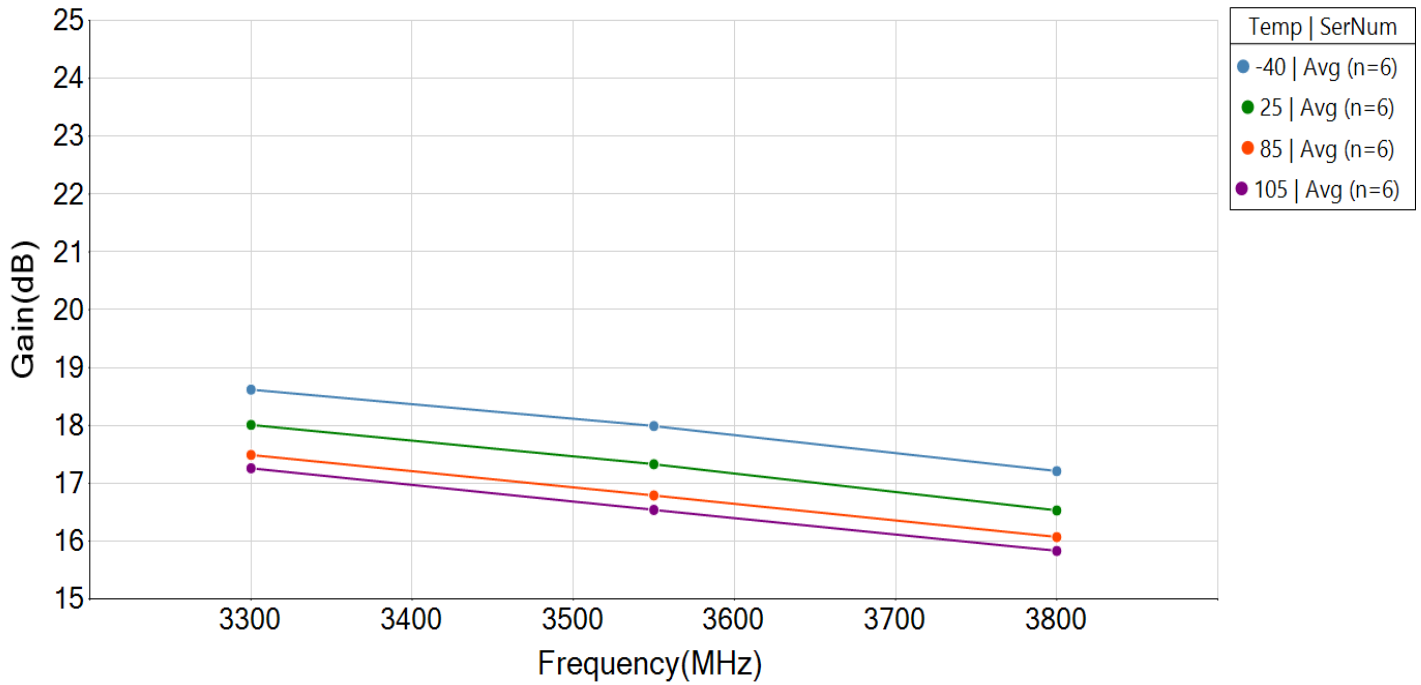
Nominal Operating Parameters – RF

The following conditions apply unless noted otherwise: Typical Application Schematic using the 3.3 to 3.8 GHz tuning set. $V_{DD} = 5\text{ V}$, $V_{EN/BYPASS} = 5\text{ V}$, $I_{DDQ} = 70\text{ mA}$. $F_{TEST} = 3.6\text{ GHz}$. $M5 = 600\ \Omega$. $T_{PKG\ BASE} = 25\text{ }^{\circ}\text{C}$. Evaluation board losses are included within the specifications.

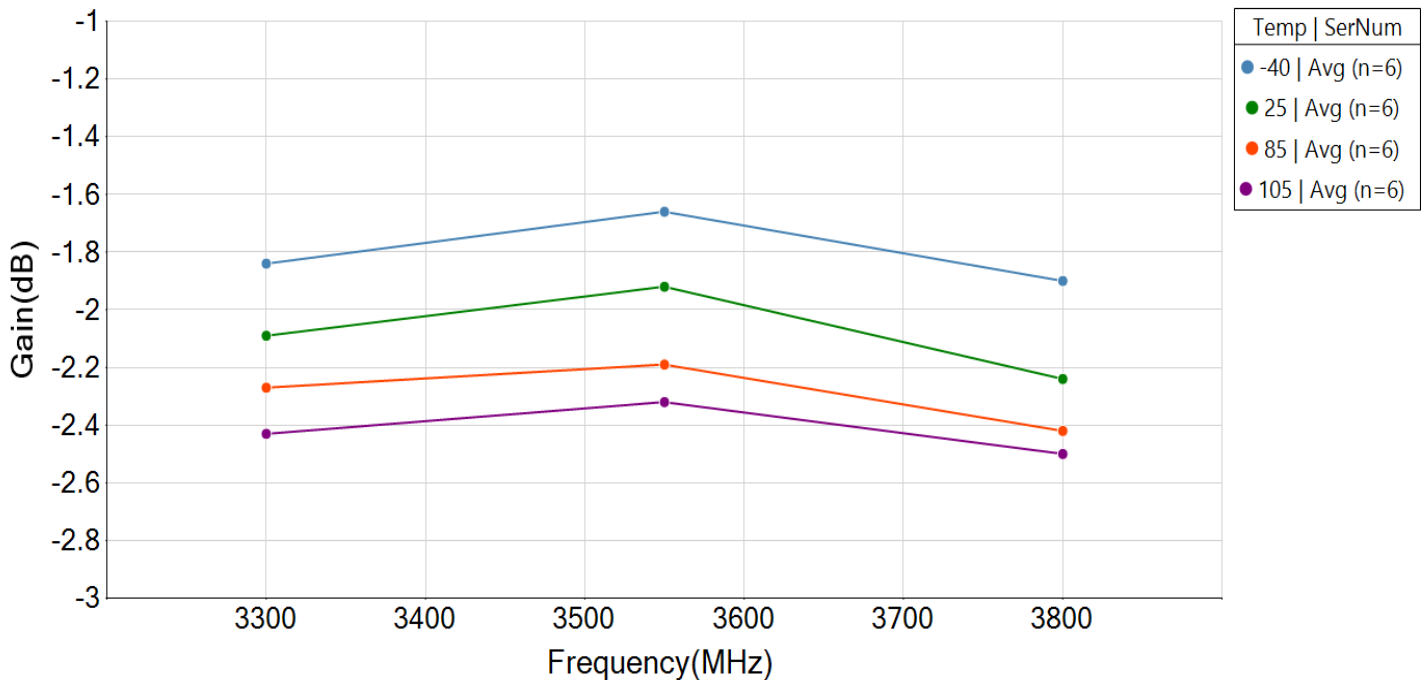
Parameter	Symbol	Specification			Unit	Condition
		Min.	Typ.	Max.		
High Gain Mode						$V_{DD} = 5\text{ V}$, $V_{EN/BYPASS} = 5\text{ V}$
Gain	S21	16	17.2		dB	
Output 3 rd Order Intercept Point	OIP3		38		dBm	+2 dBm P_{OUT} per tone at 2 MHz spacing (3599 and 3601 MHz).
Output 1 dB Compression Power	OP1dB	19.5	22		dBm	
Noise Figure	NF		1.1		dB	On standard evaluation board.
Bypass Mode						$V_{DD} = 5\text{ V}$, $V_{EN/BYPASS} = 0\text{ V}$
Gain	S21	-3.6	-2		dB	
Output 3 rd Order Intercept Point	OIP3		46		dBm	+8 dBm P_{OUT} per tone at 2 MHz spacing (3599 and 3601 MHz).
Output 1 dB Compression Power	OP1dB		21		dBm	

GRF2076 Evaluation Board Data: 3.3 to 3.8 GHz Tune

GRF2076 Gain vs Frequency at Ven(V) = 5 V

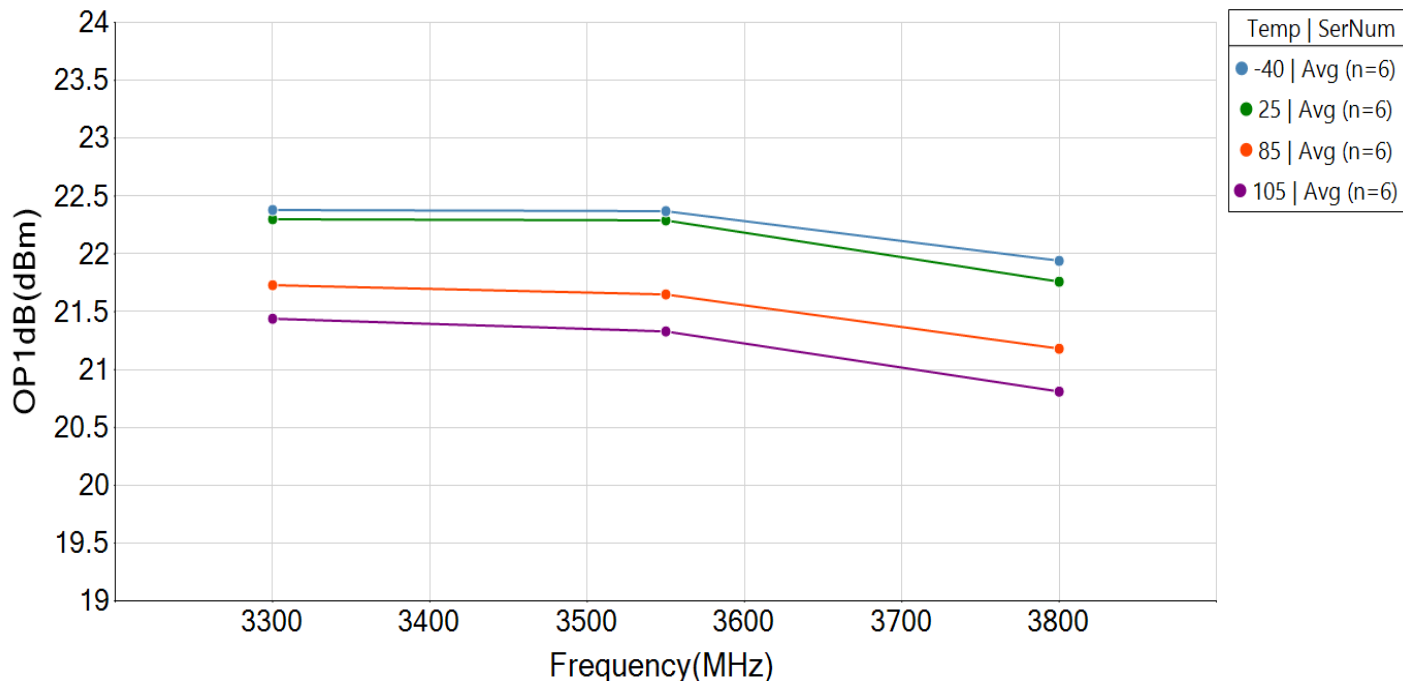


GRF2076 Gain vs Frequency at Ven(V) = 0 V

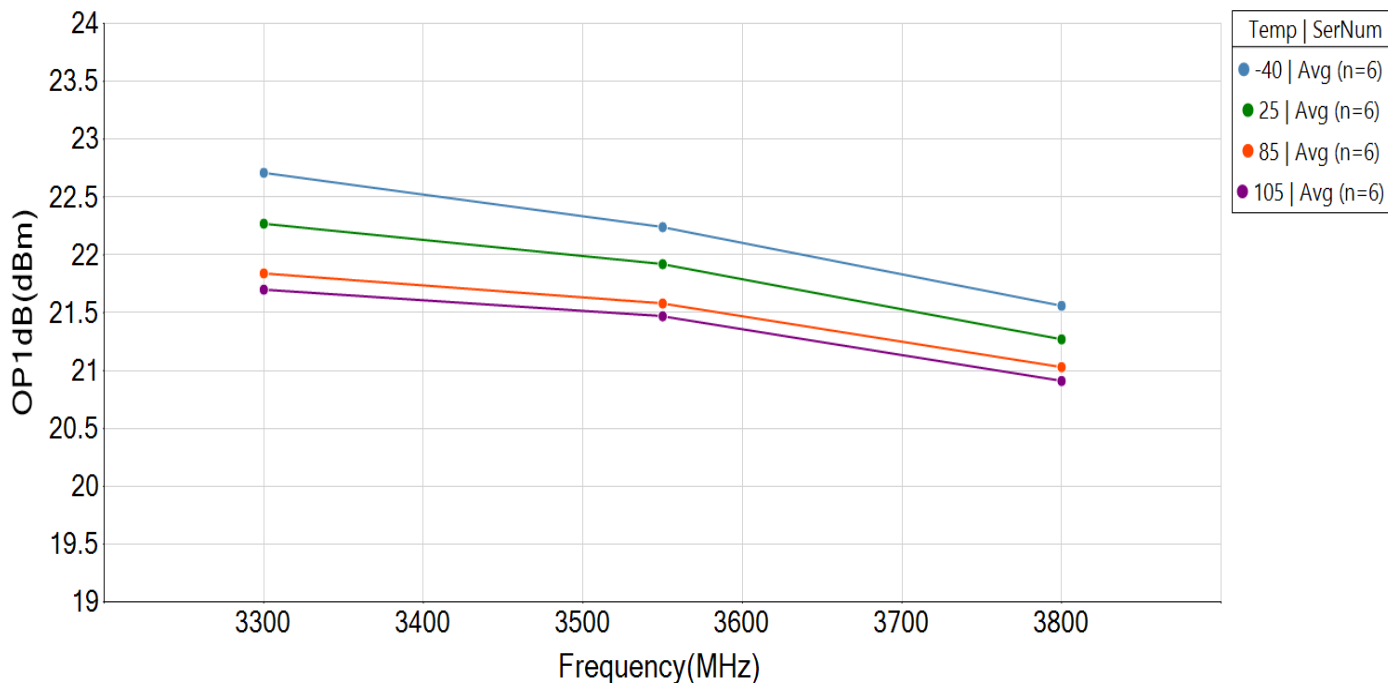


GRF2076 Evaluation Board Data: 3.3 to 3.8 GHz Tune

GRF2076 OP1dB vs Frequency at Ven(V) = 5 V

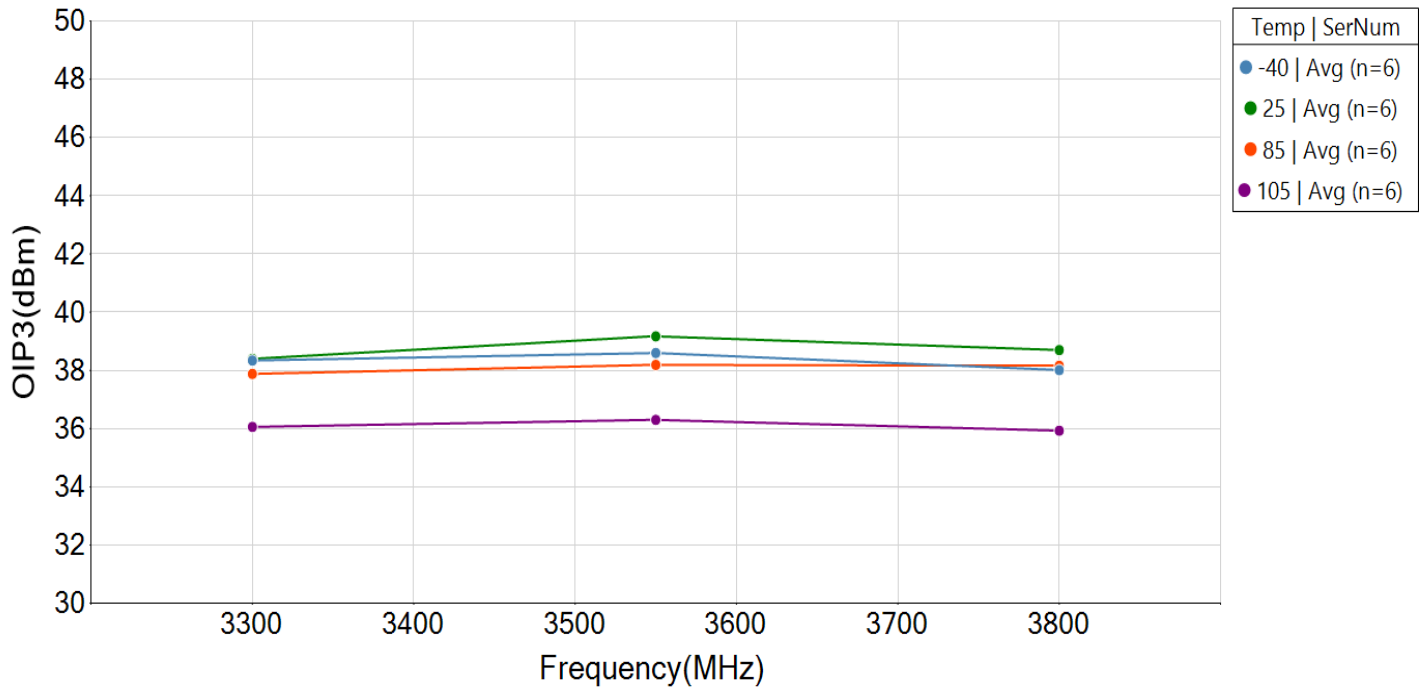


GRF2076 OP1dB vs Frequency at Ven(V) = 0 V

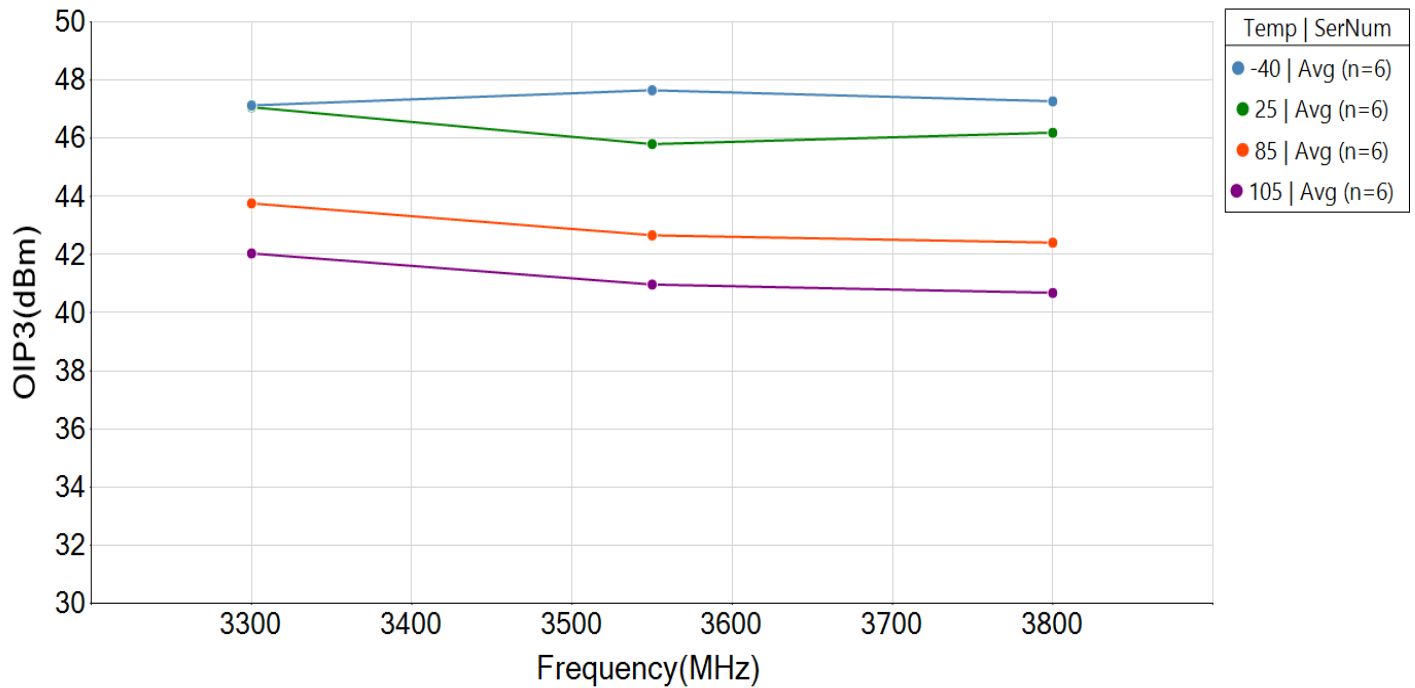


GRF2076 Evaluation Board Data: 3.3 to 3.8 GHz Tune

GRF2076 OIP3 vs Frequency at Pout = 2 dBm and Ven(V) = 5 V

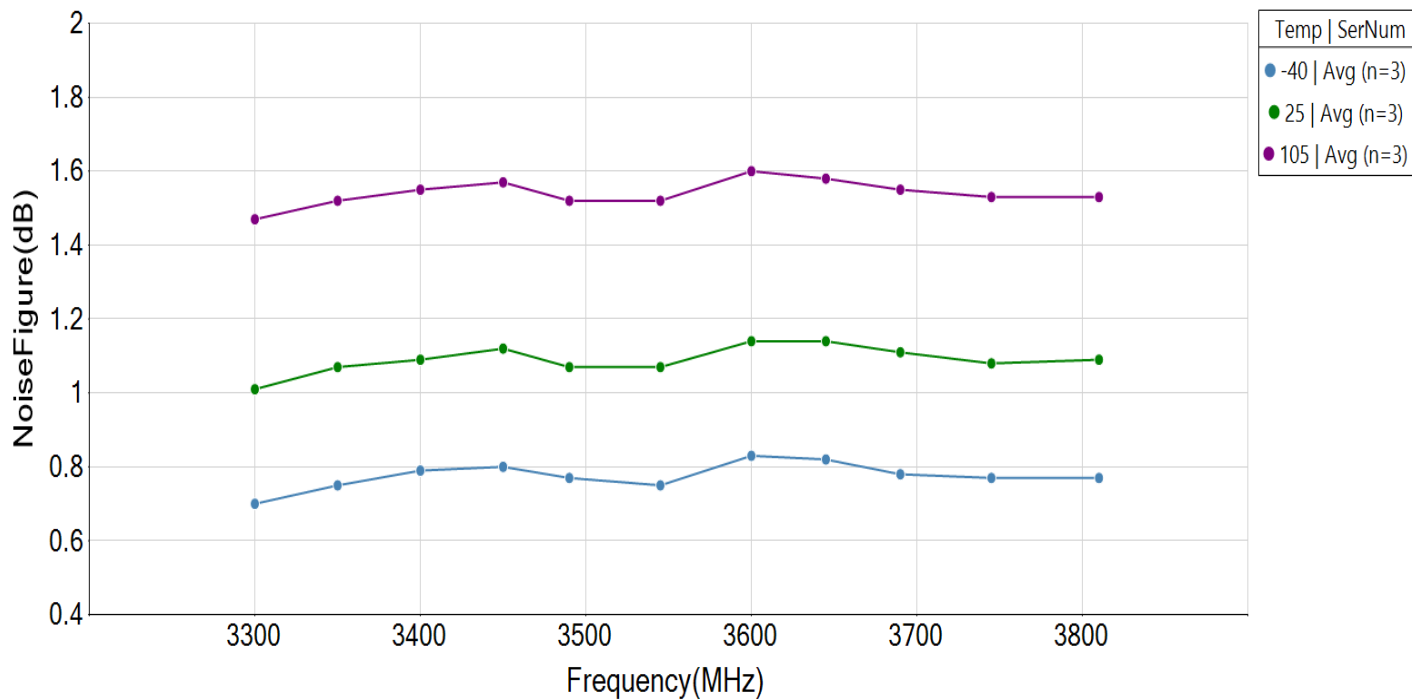


GRF2076 OIP3 vs Frequency at Pout = 8 dBm and Ven(V) = 0 V

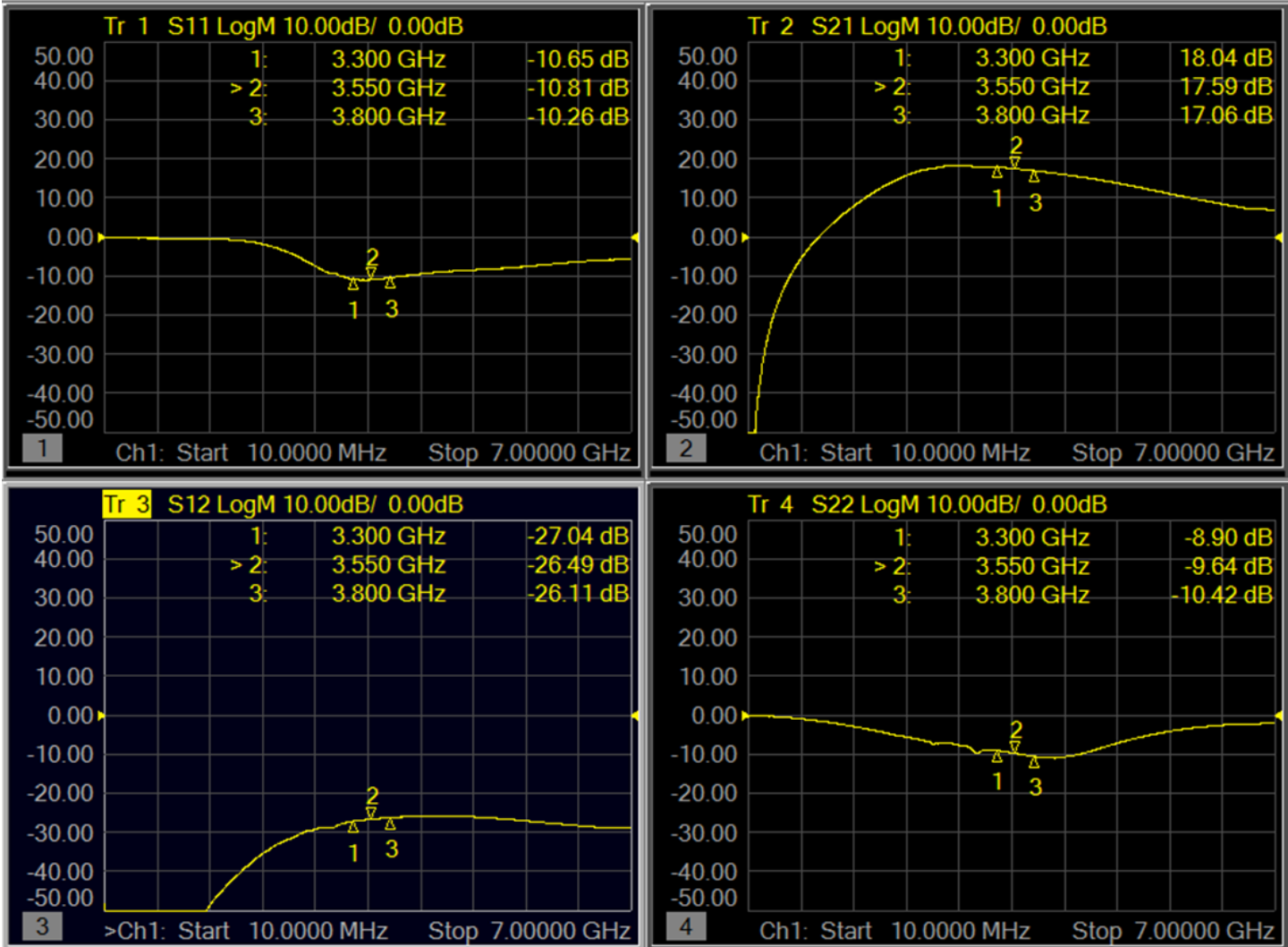


GRF2076 Evaluation Board Data: 5 V, 3.3 to 3.8 GHz Tune

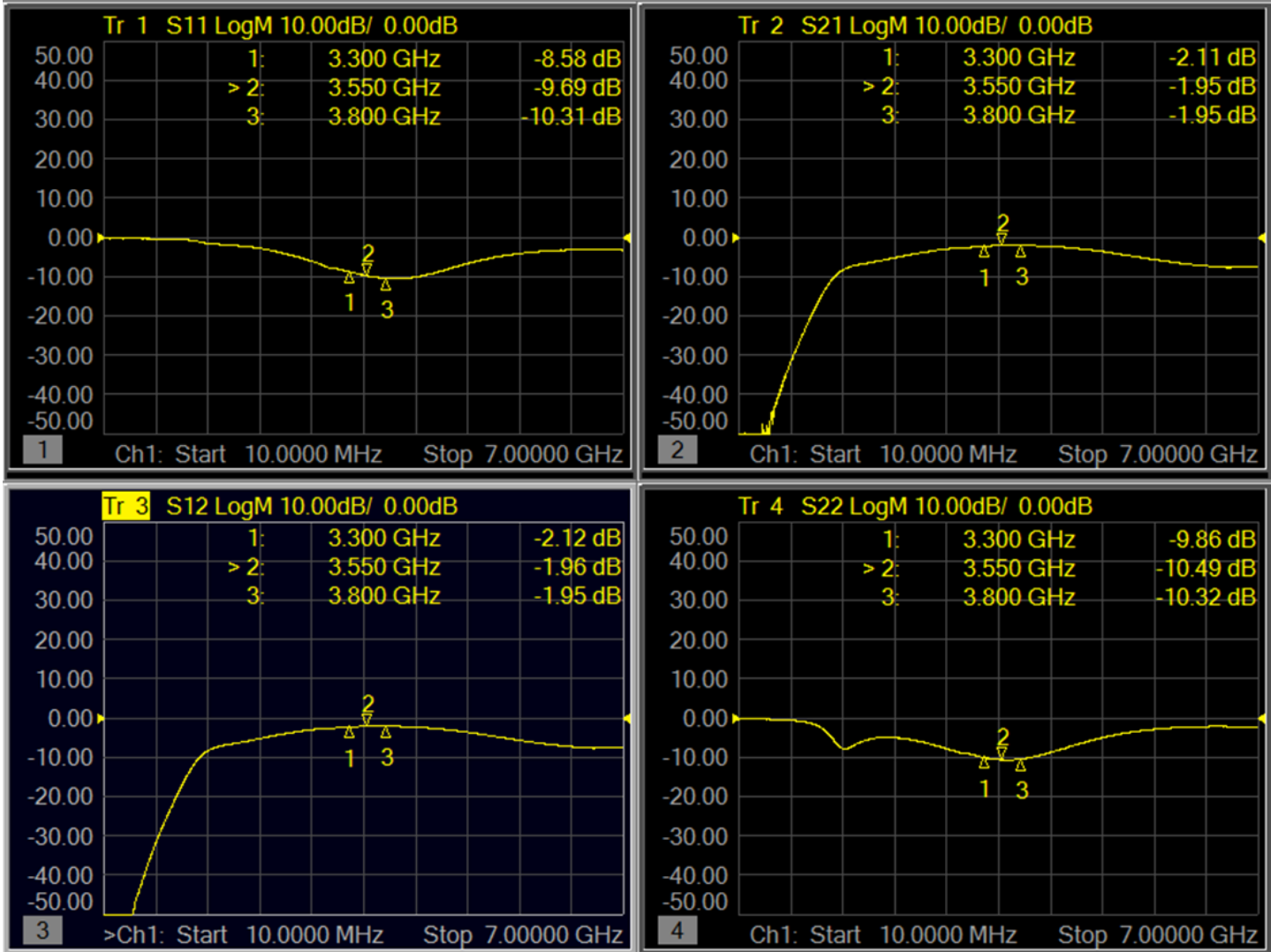
GRF2076 Noise Figure vs Frequency



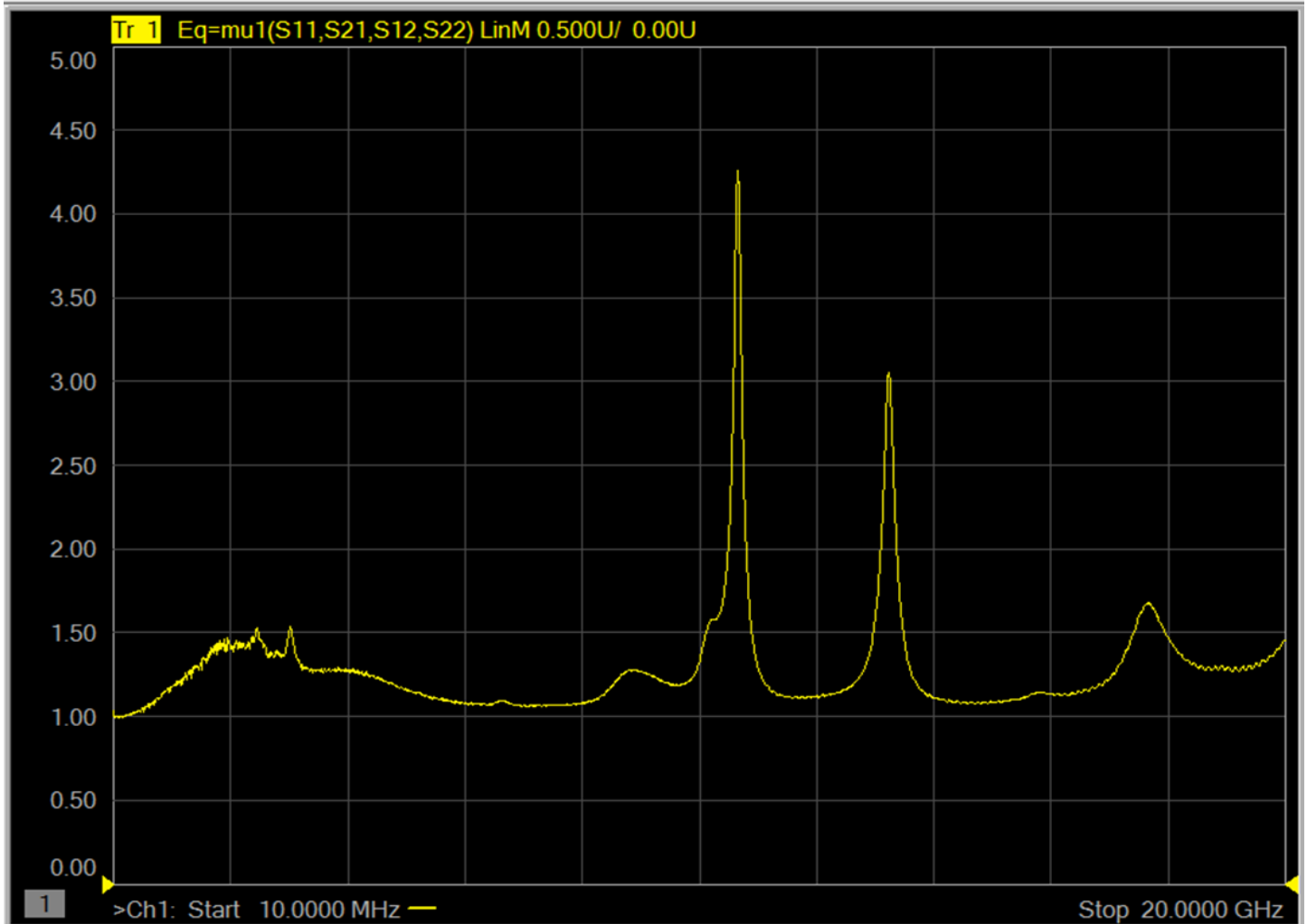
GRF2076 Evaluation Board S-Parameters: Gain Mode (3.3 to 3.8 GHz Tune)



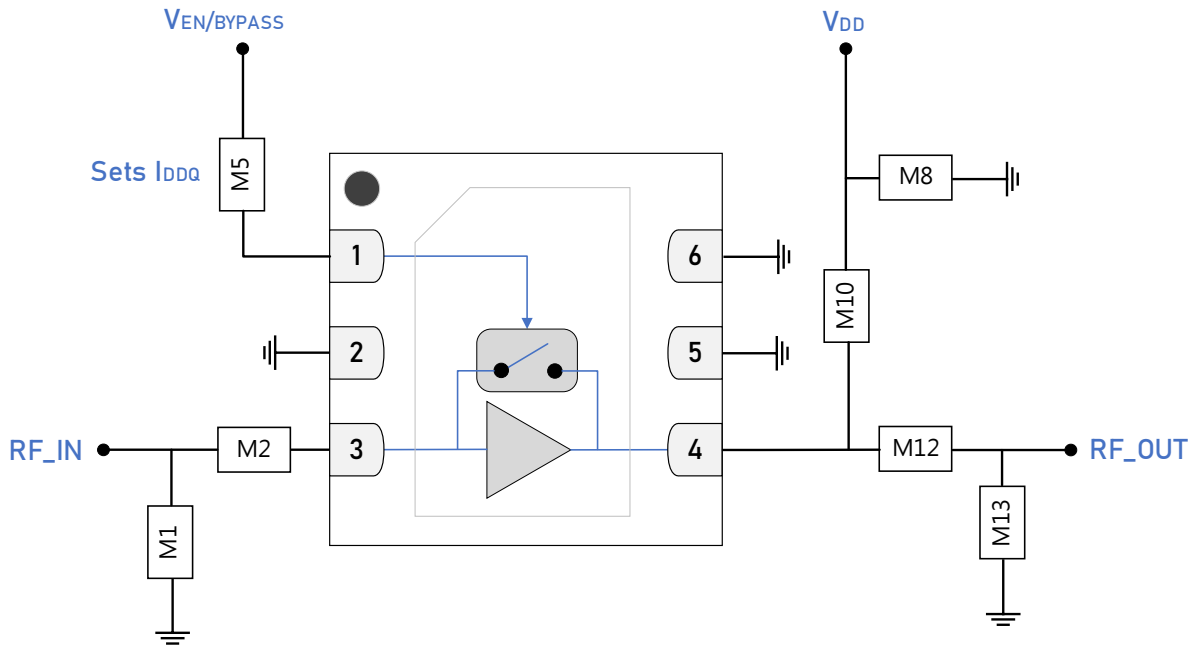
GRF2076 Evaluation Board S-Parameters: Bypass Mode (3.3 to 3.8 GHz Tune)



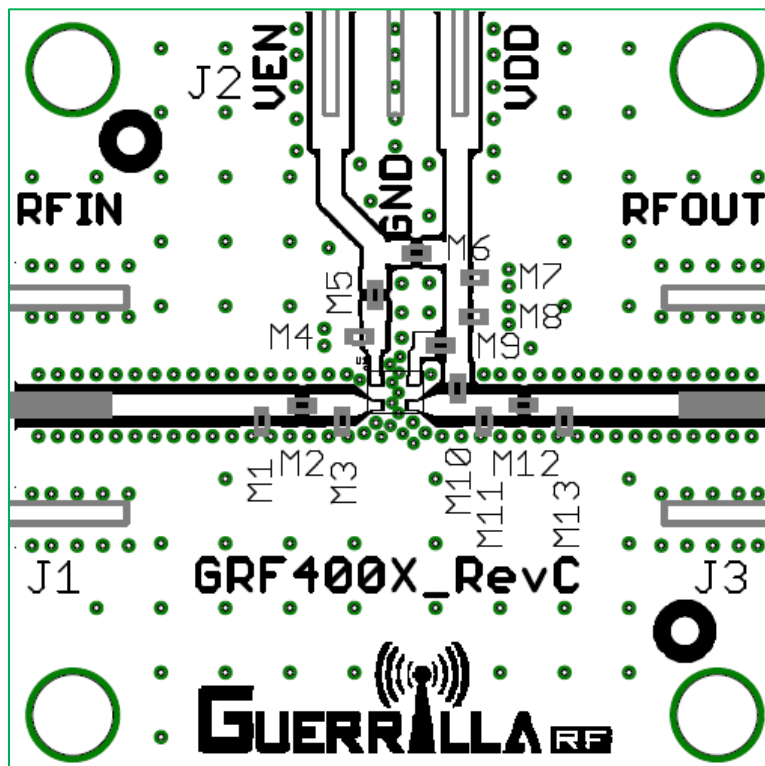
GRF2076 Evaluation Board Stability Mu Factor (10 MHz to 20 GHz)



Note: Mu factor ≥ 1.0 implies unconditional stability.



GRF2076 Standard Evaluation Board Schematic



GRF2076 Evaluation Board Assembly Diagram

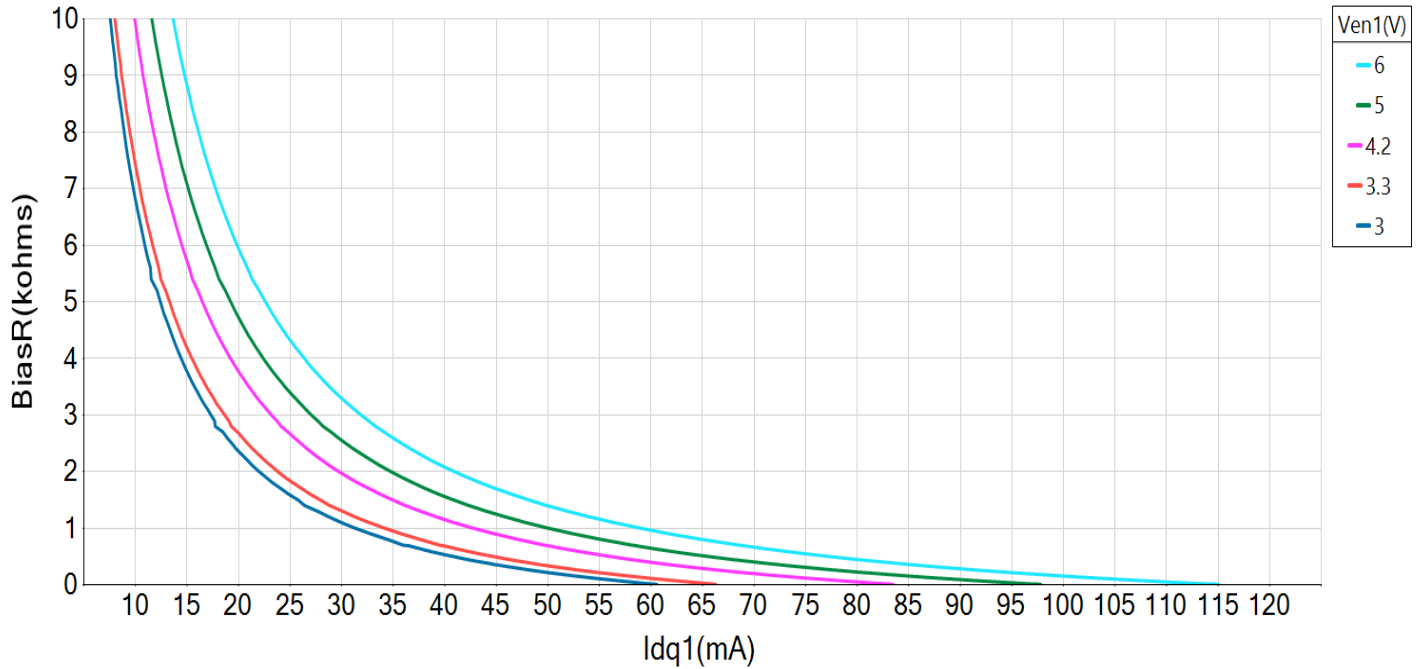


GRF2076 Evaluation Board Assembly Diagram Reference: 3.3 to 3.8 GHz Tune

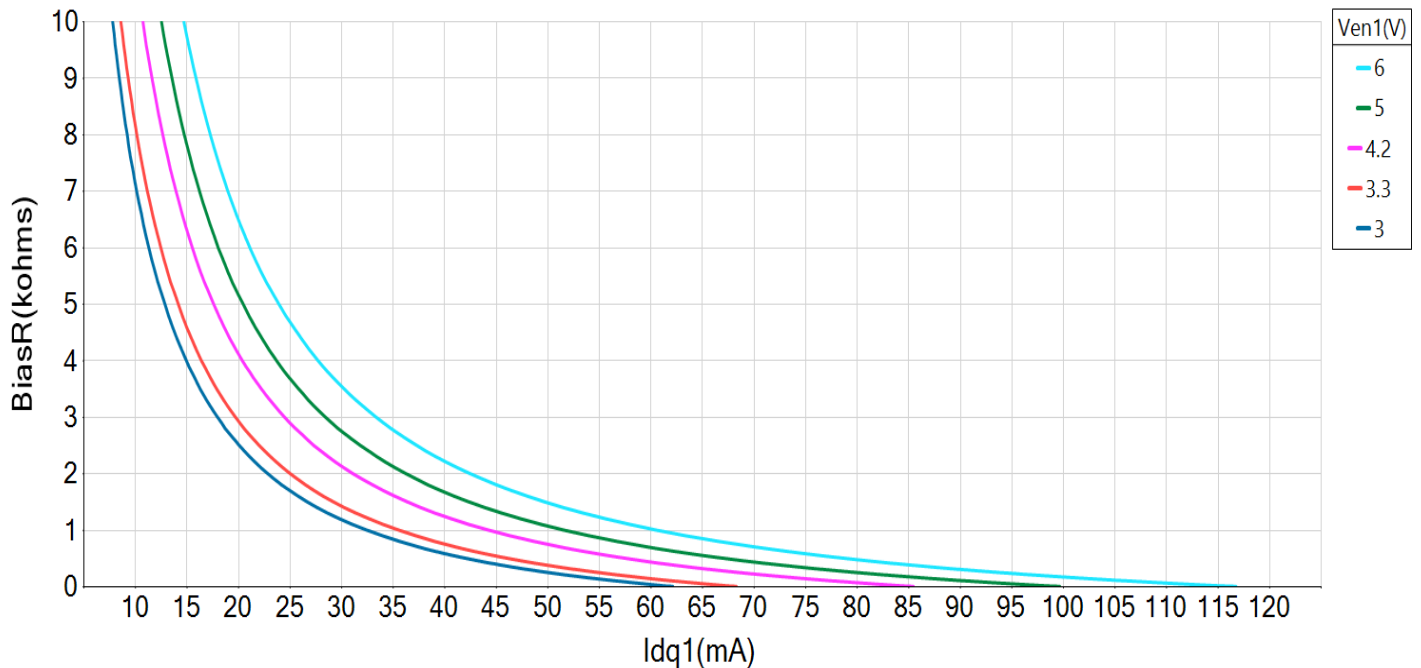
Component	Type	Manufacturer	Family	Value	Package Size	Substitution
M3, M4, M6, M7, M9, M11	DNP					
M1	Inductor	Murata	LQG	2.0 nH	0402	ok
M2	Capacitor	Murata	GJM	1.0 pF	0402	ok
M5 (sets I _{DDQ})	Resistor	Various	5%	See Curves	0402	ok
M8	Capacitor	Murata	GRM	0.1 µF	0402	ok
M10	Inductor	Murata	LQG	1.8 nH	0402	ok
M12	Capacitor	Murata	GRM	10.0 pF	0402	ok
M13	Capacitor	Murata	GRM	0.2 pF	0402	ok
Evaluation Board	GRF400X_RevC					

GRF2076 Bias Resistor Selection Curves

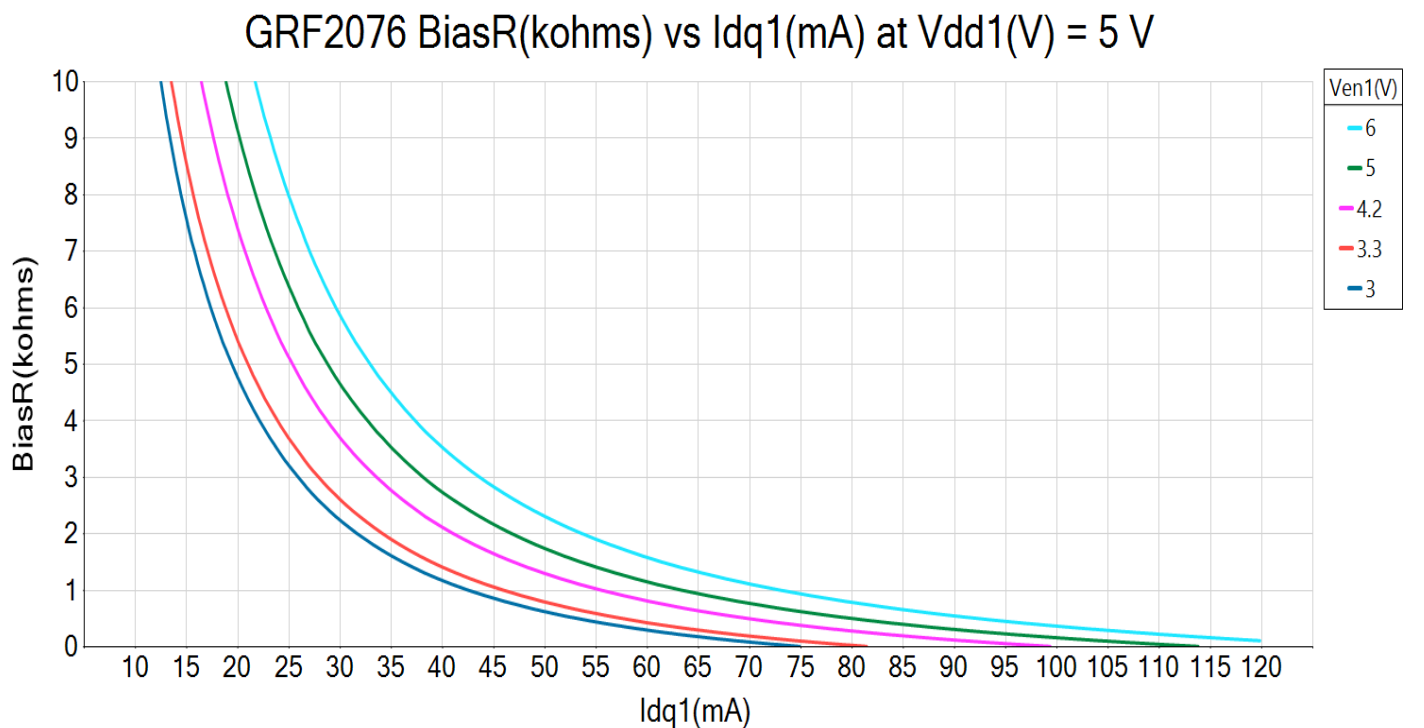
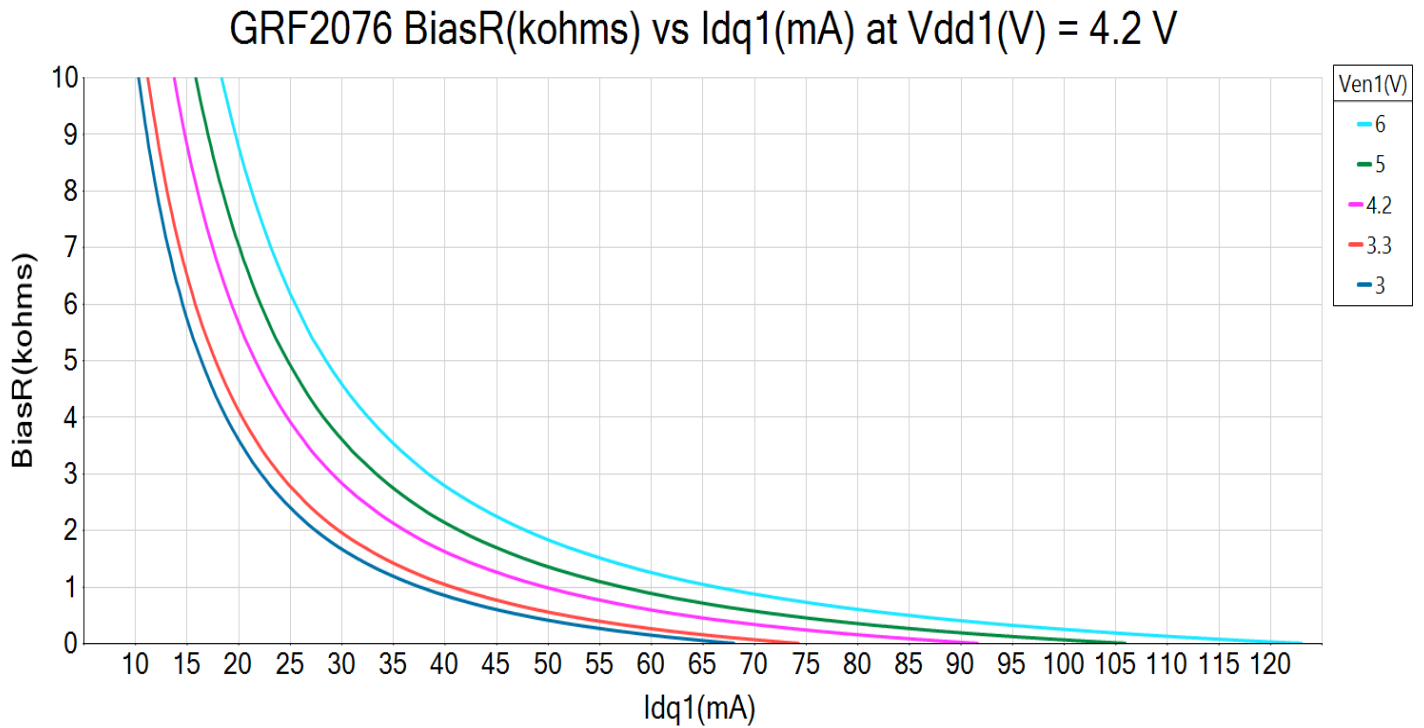
GRF2076 BiasR(kohms) vs Idq1(mA) at Vdd1(V) = 3 V



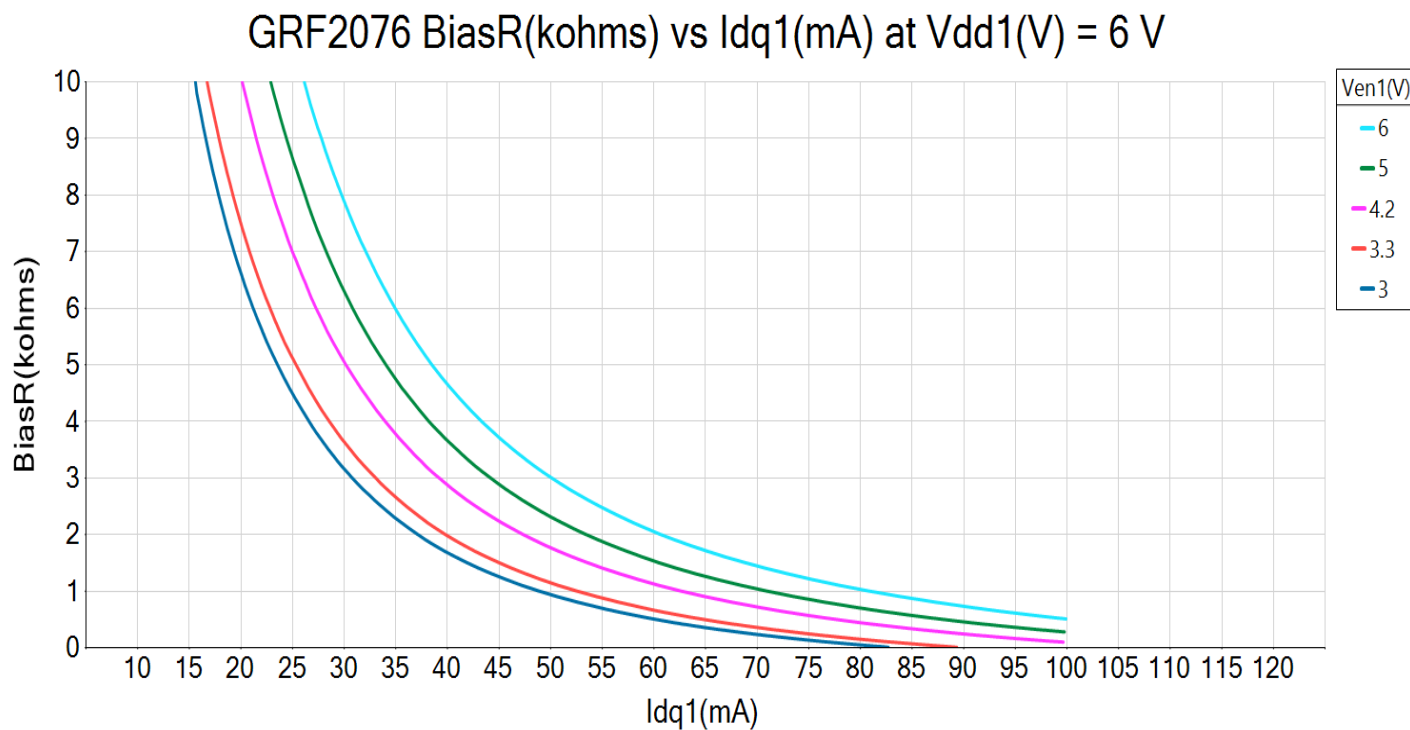
GRF2076 BiasR(kohms) vs Idq1(mA) at Vdd1(V) = 3.3 V

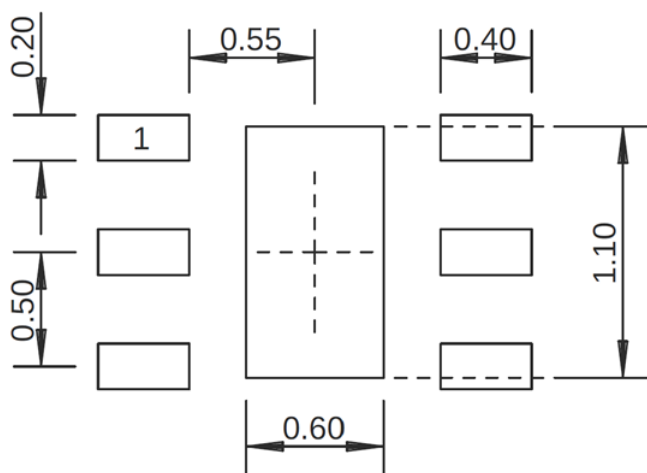


GRF2076 Bias Resistor Selection Curves

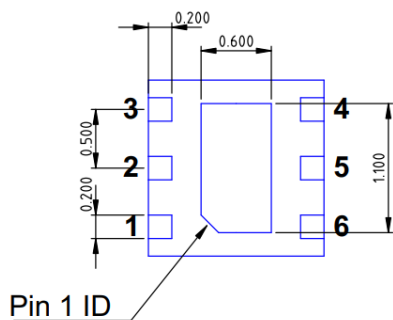


GRF2076 Bias Resistor Selection Curves

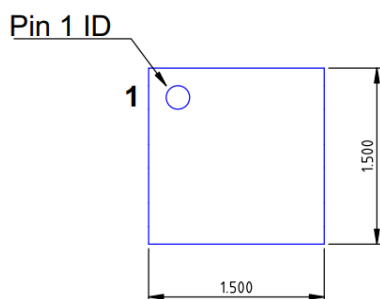




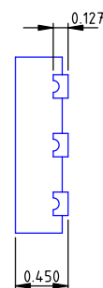
1.5 x 1.5 mm DFN-6 Suggested PCB Footprint (Top View)



Bottom View



Top View



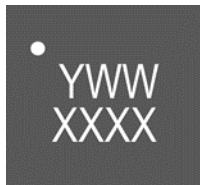
Side View

DFN6 1.5x1.5mm

Dimensions in millimeters
Dimensional Tolerance: ± 0.05

1.5 x 1.5 mm DFN-6 Package Dimensions

Package Marking Diagram



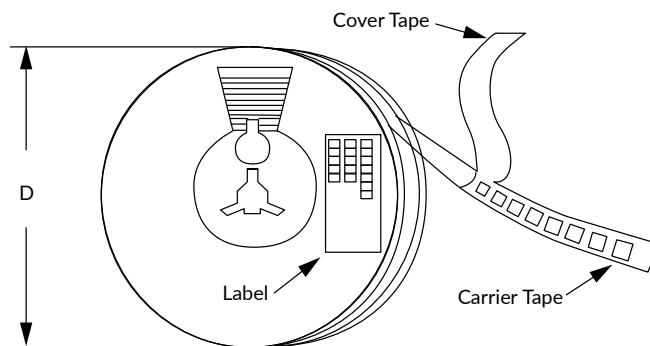
- Line 1: "Y" = YEAR (single digit). "WW" = WORK WEEK the Device was assembled.
- Line 2: "XXXX" = Device PART NUMBER.

Tape and Reel Information

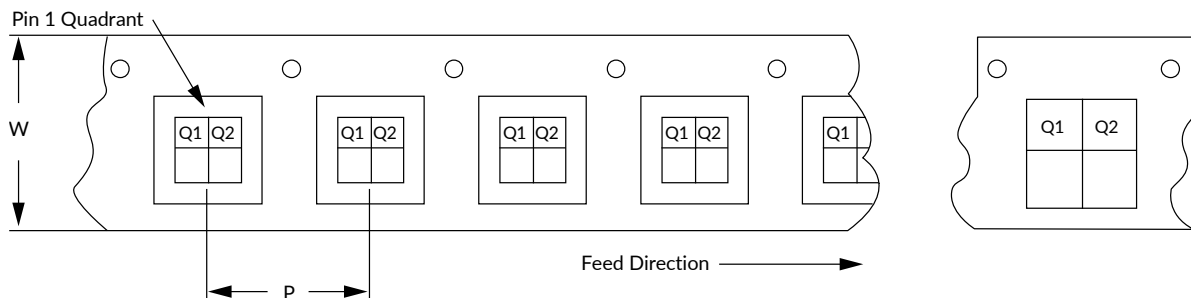
Guerrilla RF's tape and reel specification complies with Electronics Industries Alliance (EIA) standards for "Embossed Carrier Tape of Surface Mount Components for Automatic Handling" (reference EIA-481). See the following page for the Tape and Reel Specification and Device Package Information table, which includes units per reel.

Devices are loaded with pins down into the carrier pocket with protective cover tape and reeled onto a plastic reel. Each reel is packaged in a cardboard box. There are product labels on the reel, the protective ESD bag and the outside surface of the box.

For the Tape and Reel Reference Table, please refer to: [Package Manufacturing Information | Guerrilla RF \(guerrilla-rf.com\)](#)



Tape and Reel Packaging with Reel Diameter Noted (D)



Carrier Tape Width (W), Pitch (P), Feed Direction and Pin 1 Quadrant Information



Revision History

Revision Date	Description of Change
April 13, 2020	Preliminary Data Sheet.
November 8, 2022	Release Ø Data Sheet. Upgraded Data Sheet to new format. Added new characterization plots. Added new bias resistor selection curves. Lowered OP1dB lower limit from 21.5 to 19.5 dBm.
December 20, 2022	Raised RF input power ($P_{IN\ MAX}$) from 22 to 27 dBm in Gain mode. Added RF input power ($P_{IN\ MAX}$) in Bypass mode.
April 29, 2025	Raised Maximum Operating Temperature from 105 to 115 °C.
May 9, 2025	Extended upper frequency range from 6000 MHz to 7125 MHz.
December 18, 2025	Changed evaluation board to GRF400X_RevC.



Data Sheet Classifications

Data Sheet Status	Notes
Advance	S-parameter and NF data based on EM simulations for the fully packaged device using foundry-supplied transistor S-parameters. Linearity estimates based on device size, bias condition and experience with related devices.
Preliminary	All data based on limited evaluation board measurements taken within the Guerrilla RF Applications Lab. All parametric values are subject to change pending the collection of additional data.
Release Ø	All data based on measurements taken with <i>production-released</i> material. TYP values are based on a combination of ATE and bench-level measurements, with MIN/MAX limits defined using <i>modelled estimates</i> that account for part-to-part variations and expected process spreads. Although unlikely, future refinements to the TYP/MIN/MAX values may be in order as multiple lots are processed through the factory.
Release A-Z	All data based on measurements taken with production-released material <i>derived from multiple lots which have been fabricated over an extended period of time</i> . MIN/MAX limits may be refined over previous releases as more statistically significant data is collected to account for process spreads.

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